

# MOSFET - N-Channel Shielded Gate PowerTrench® 150 V, 15 mΩ, 61.3 A



ON Semiconductor®

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## NVDS015N15MC

### Features

- Shielded Gate MOSFET Technology
- Max  $R_{DS(on)}$  = 15 mΩ at  $V_{GS} = 10$  V,  $I_D = 29$  A
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Primary Side for 48 V Isolated Bus
- SR for MV Secondary Applications

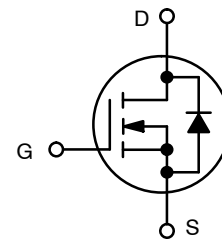
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	150	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$ 61.3 A
		$T_C = 100^\circ\text{C}$	43.4
Power Dissipation $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$ 107.1 W
		$T_C = 100^\circ\text{C}$	53.6
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ 10.5 A
		$T_A = 100^\circ\text{C}$	7.4
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 3.1 W
		$T_A = 100^\circ\text{C}$	1.6
Pulsed Drain Current	$T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$	$I_{DM}$ 382	A
Operating Junction and Storage Temperature Range	$T_J$ , $T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	89.3	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 4.4$ A)	$E_{AS}$	1301	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

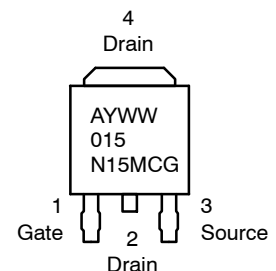
1. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	$I_D$ MAX
150 V	15 mΩ @ 10 V	61.3 A



N-CHANNEL MOSFET

### MARKING DIAGRAM



015N15MCG = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

### ORDERING INFORMATION

Device	Package	Shipping†
NVDS015N15MCT4G	DPAK (Pb-Free)	2500 / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	1.4	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	47.9	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	150			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$ , ref to $25^\circ\text{C}$		83		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 120\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		1.1	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 162\ \mu\text{A}$	2.5		4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 162\ \mu\text{A}$ , ref to $25^\circ\text{C}$		-8.2		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 29\text{ A}$		11.8	15	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 29\text{ A}$		58		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 75\text{ V}$		2120		pF
Output Capacitance	$C_{OSS}$			595		
Reverse Transfer Capacitance	$C_{RSS}$			10.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}; I_D = 29\text{ A}$		27		nC
Threshold Gate Charge	$Q_{G(TH)}$			7		
Gate-to-Source Charge	$Q_{GS}$			11		
Gate-to-Drain Charge	$Q_{GD}$			4		
Plateau Voltage	$V_{GP}$			5.5		

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DD} = 75\text{ V}, I_D = 29\text{ A}, R_G = 6\ \Omega$		16		ns
Rise Time	$t_r$			5		
Turn-Off Delay Time	$t_{d(OFF)}$			21		
Fall Time	$t_f$			4		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 29\text{ A}$	$T_J = 25^\circ\text{C}$		0.89	1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$ $di_S/dt = 300\text{ A}/\mu\text{s}, I_S = 29\text{ A}$			49		ns
Reverse Recovery Charge	$Q_{RR}$					197	
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$ $di_S/dt = 1000\text{ A}/\mu\text{s}, I_S = 29\text{ A}$			34		ns
Reverse Recovery Charge	$Q_{RR}$					345	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

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## TYPICAL CHARACTERISTICS

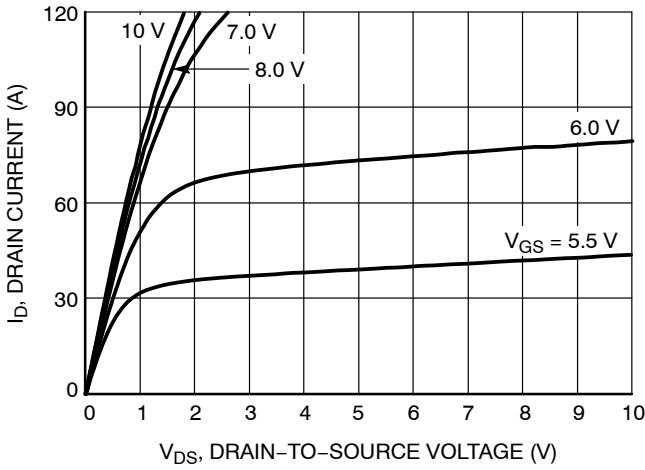


Figure 1. On-Region Characteristics

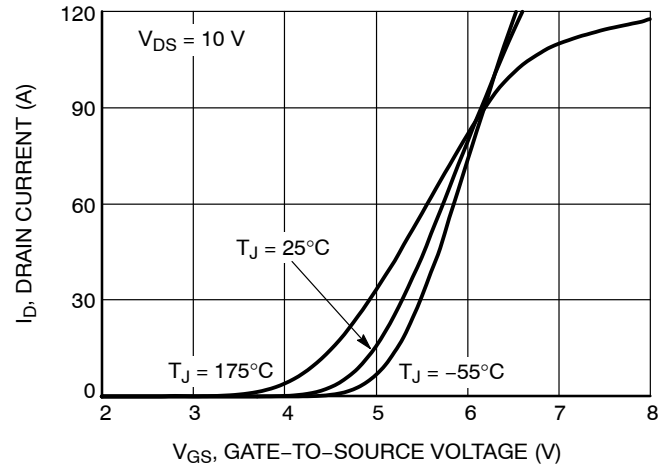


Figure 2. Transfer Characteristics

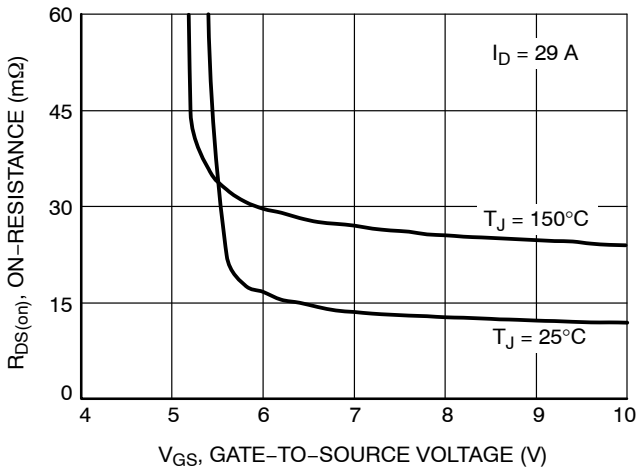


Figure 3. On-Resistance vs. Gate-to-Source Voltage

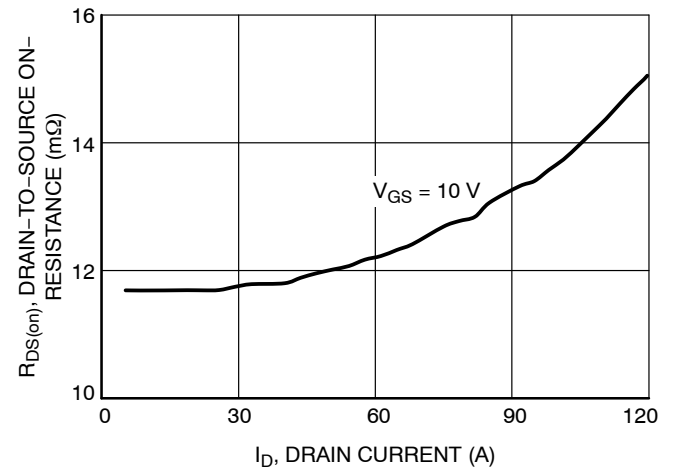


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

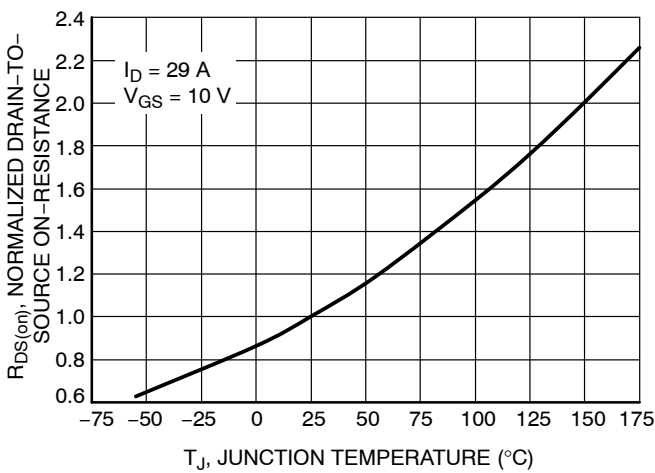


Figure 5. Normalized On-Resistance vs. Junction Temperature

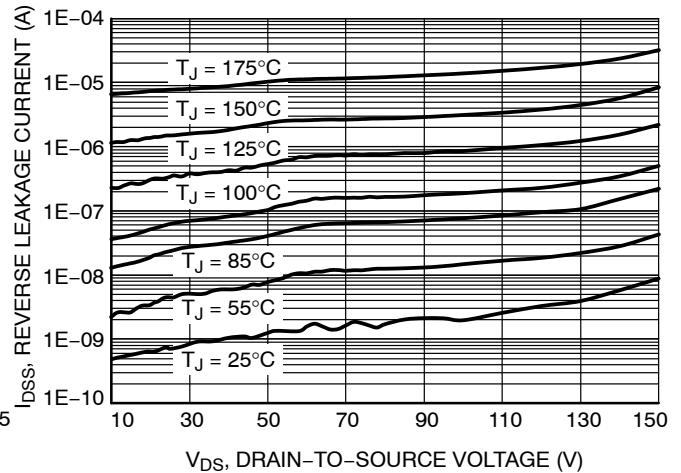
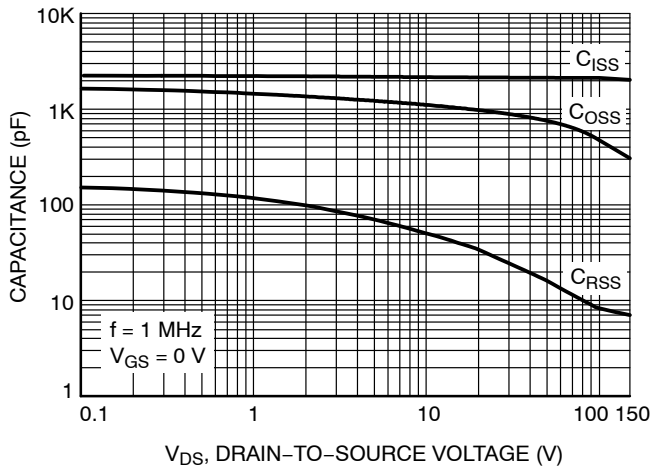


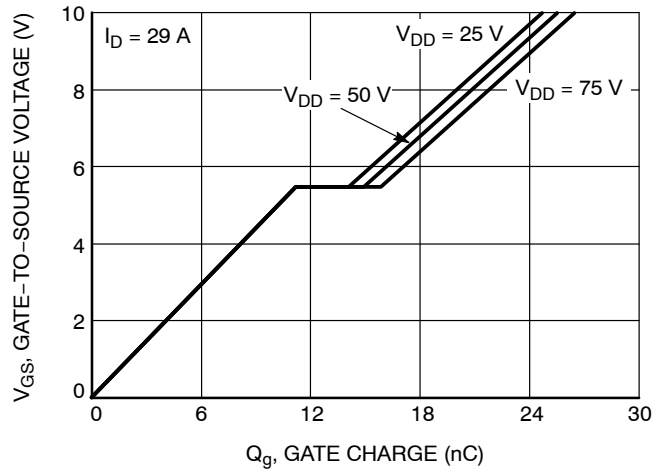
Figure 6. Drain-to-Source Leakage Current vs. Voltage

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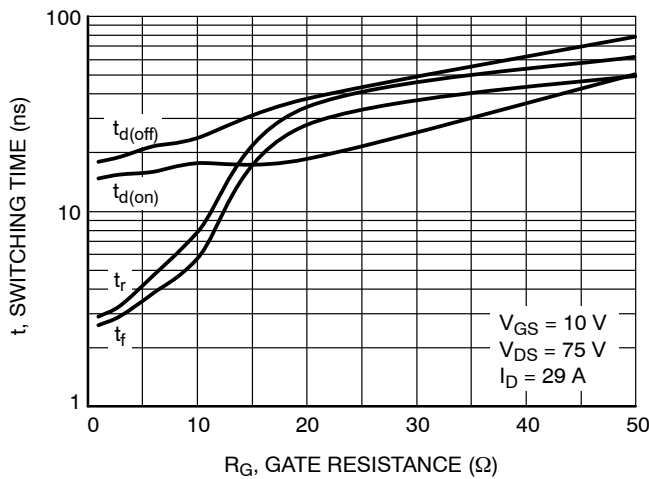
## TYPICAL CHARACTERISTICS



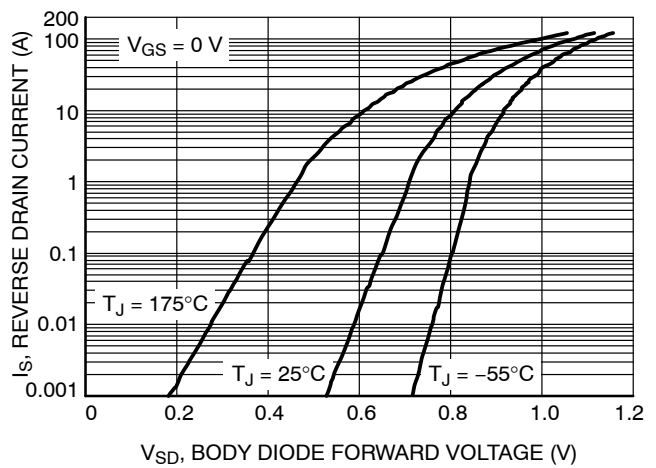
**Figure 7. Capacitance vs. Drain-to-Source Voltage**



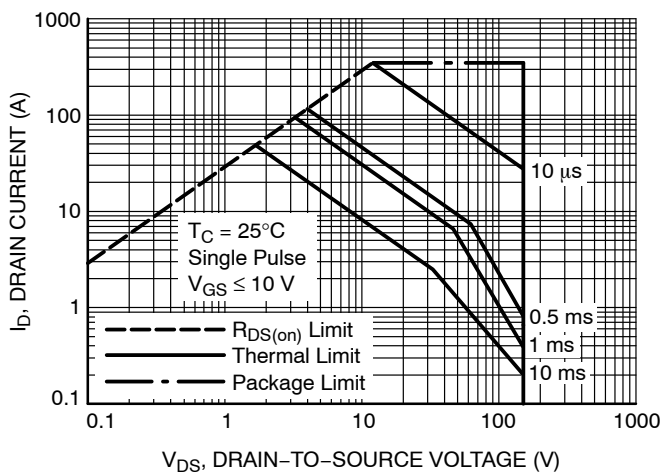
**Figure 8. Gate Charge Characteristics**



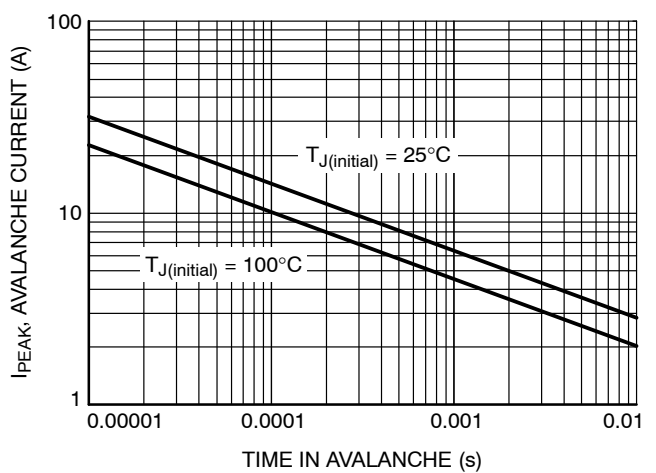
**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**



**Figure 10. Source-to-Drain Diode Forward Voltage vs. Source Current**



**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Unclamped Inductive Switching Capability**

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## TYPICAL CHARACTERISTICS

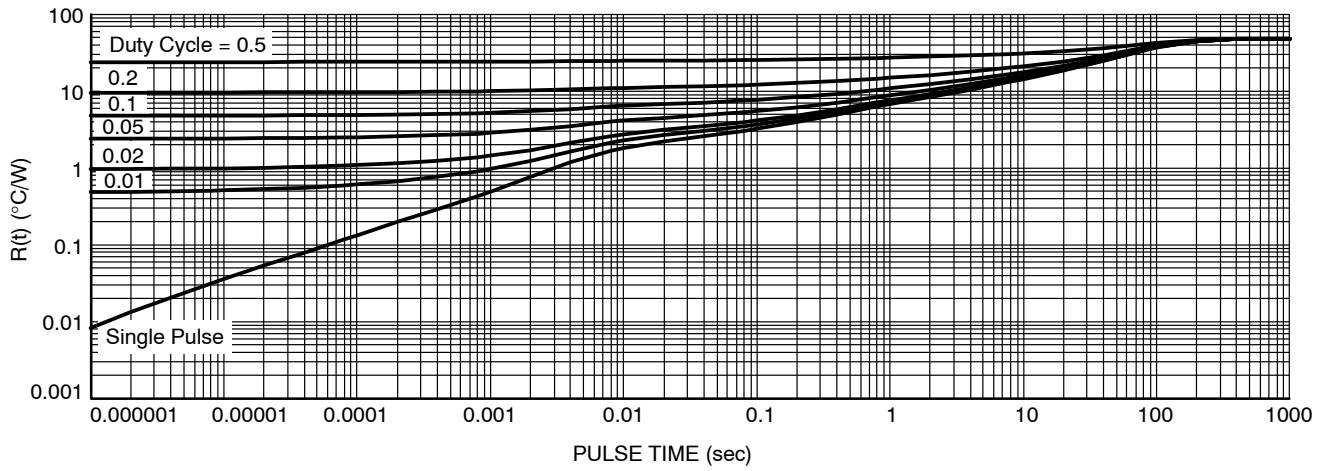


Figure 13. Transient Thermal Impedance

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## DPAK (SINGLE GAUGE) CASE 369C ISSUE F

DATE 21 JUL 2015

SCALE 1:1



**NOTES:**

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

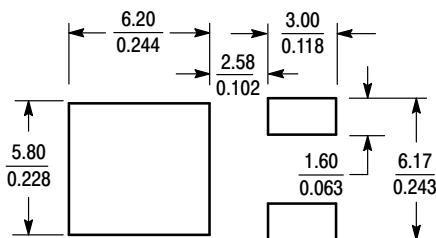
### GENERIC MARKING DIAGRAM\*

- |   |   |  |  |   |
|---|---|--|--|---|
| <p><b>STYLE 1:</b><br/>PIN 1. BASE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> | <p><b>STYLE 2:</b><br/>PIN 1. GATE<br/>2. DRAIN<br/>3. SOURCE<br/>4. DRAIN</p>          | <p><b>STYLE 3:</b><br/>PIN 1. ANODE<br/>2. CATHODE<br/>3. ANODE<br/>4. CATHODE</p> | <p><b>STYLE 4:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. GATE<br/>4. ANODE</p>              | <p><b>STYLE 5:</b><br/>PIN 1. GATE<br/>2. ANODE<br/>3. CATHODE<br/>4. ANODE</p>     |
| <p><b>STYLE 6:</b><br/>PIN 1. MT1<br/>2. MT2<br/>3. GATE<br/>4. MT2</p>                 | <p><b>STYLE 7:</b><br/>PIN 1. GATE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> | <p><b>STYLE 8:</b><br/>PIN 1. N/C<br/>2. CATHODE<br/>3. ANODE<br/>4. CATHODE</p>   | <p><b>STYLE 9:</b><br/>PIN 1. ANODE<br/>2. CATHODE<br/>3. RESISTOR ADJUST<br/>4. CATHODE</p> | <p><b>STYLE 10:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. ANODE</p> |



- XXXXXX = Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

### SOLDERING FOOTPRINT\*



SCALE 3:1  $\left( \frac{\text{mm}}{\text{inches}} \right)$

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>DPAK (SINGLE GAUGE)</b>	<b>PAGE 1 OF 1</b>

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